NIKO-SEM

P-Channel Logic Level Enhancement Mode Field Effect Transistor

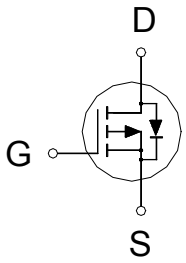
P3506DD

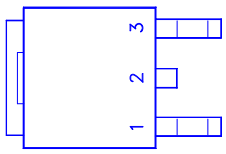
TO-252

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-60V	35mΩ	-26A





1. GATE
2. DRAIN
3. SOURCE

RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	-26	A
	T_C = 100 °C		-16	
Pulsed Drain Current[1]		I_{DM}	-100	
Avalanche Current		I_{AS}	-39	
Avalanche Energy [2]	L = 0.1mH	E_{AS}	77	mJ
Power Dissipation	T_c = 25 °C	P_D	42	W
	T_c = 100 °C		17	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3	°C / W
Junction-to-Ambient	$R_{\theta JA}$		50	°C / W

[1]Pulse width limited by maximum junction temperature.
[2]V_{DD} = -30V . Starting T_J = 25°C.

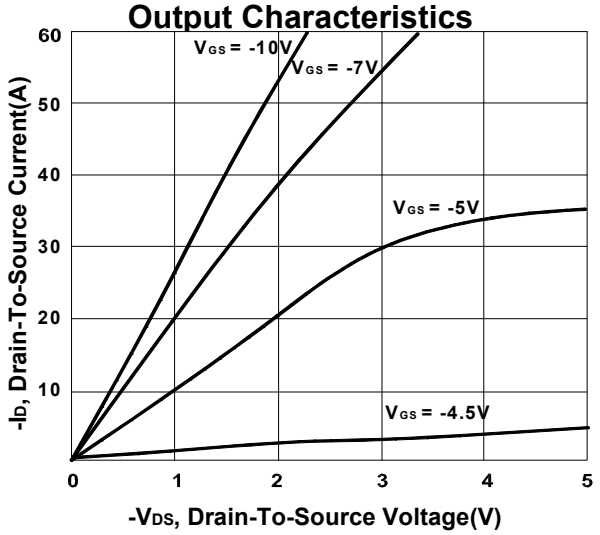
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	-2	-2.7	-4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -48V, V_{GS} = 0V			1	μA
		V_{DS} = -40V, V_{GS} = 0V, T_J = 55 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = -7V, I_D = -20A		32	55	mΩ
		V_{GS} = -10V, I_D = -25A		29	35	
Forward Transconductance[1]	g_{fs}	V_{DS} = -5V, I_D = -25A		15		S

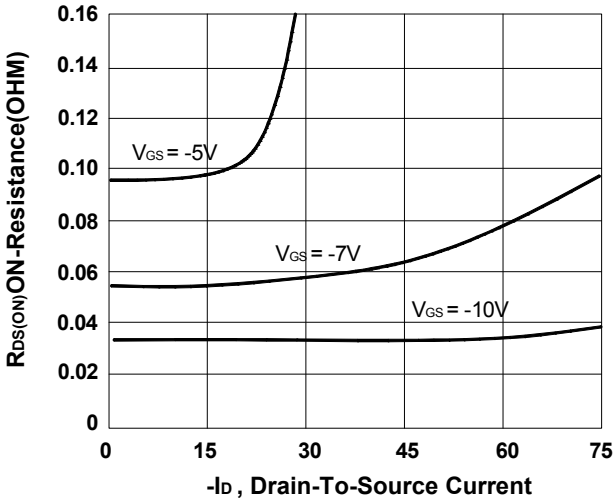
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = -5V, V_{GS} = -10V,	-100			A
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -30V, f = 1MHz		2550		pF
Output Capacitance	C_{oss}			241		
Reverse Transfer Capacitance	C_{rss}			140		
Gate Resistance	R_g	V_{GS} =0V, V_{DS} = 0V, f = 1MHz		4.85		Ω
Total Gate Charge[2]	Q_g	V_{DS} = 0.5$V_{(BR)DSS}$, V_{GS} = -10V, I_D =-25A		39		nC
Gate-Source Charge[2]	Q_{gs}			13		
Gate-Drain Charge[2]	Q_{gd}			8		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = -30V , R_L = 1Ω $I_D \cong$ -20A, V_{GS} = -10V, R_{GEN} =6Ω		30		nS
Rise Time[2]	t_r			90		
Turn-Off Delay Time[2]	$t_{d(off)}$			70		
Fall Time[2]	t_f			15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				-26	A
Forward Voltage[1]	V_{SD}	I_F = -25A, V_{GS} = 0V			-1.3	V
Reverse Recovery Time	t_{rr}	I_F = -25A, dI_F/dt = 100A / μS		30		nS
Reverse Recovery Charge	Qrr			100		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

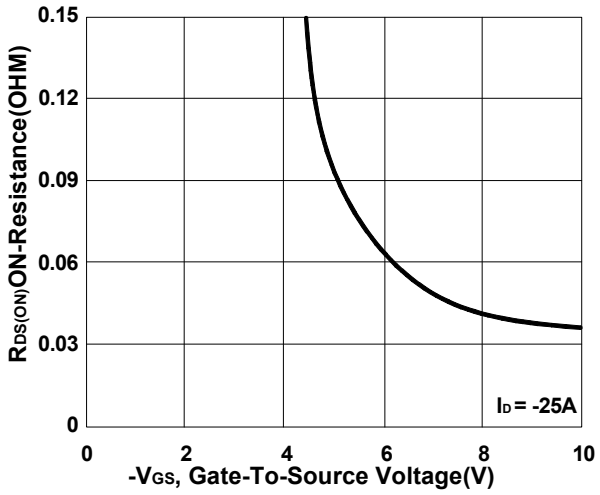
Output Characteristics



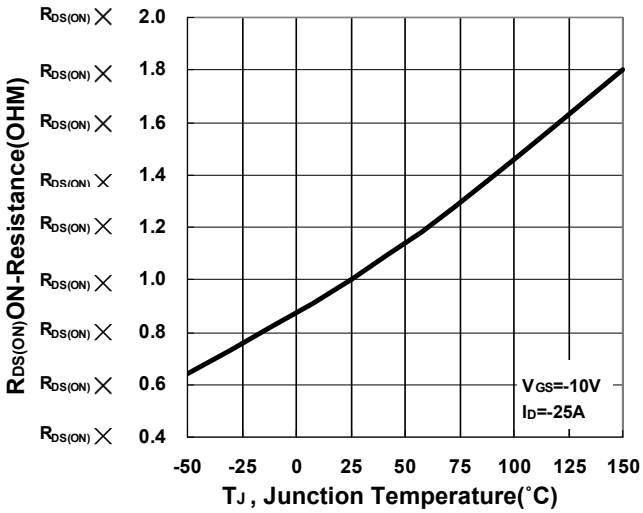
On-Resistance VS Drain Current



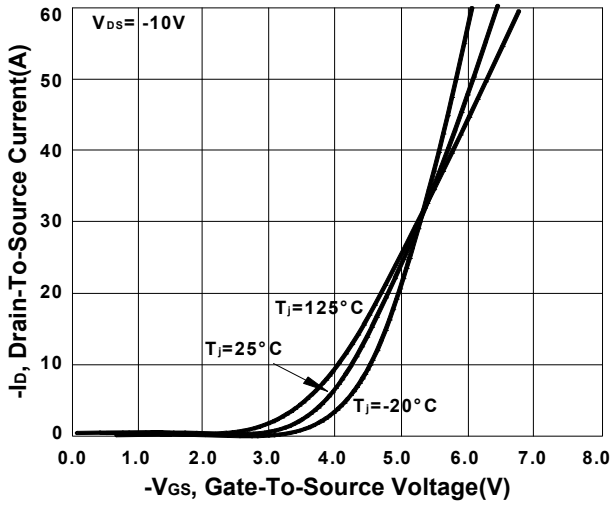
On-Resistance VS Gate-To-Source



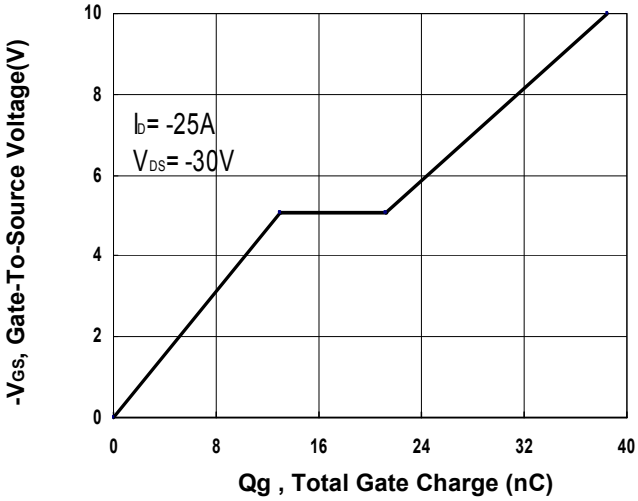
On-Resistance VS Temperature



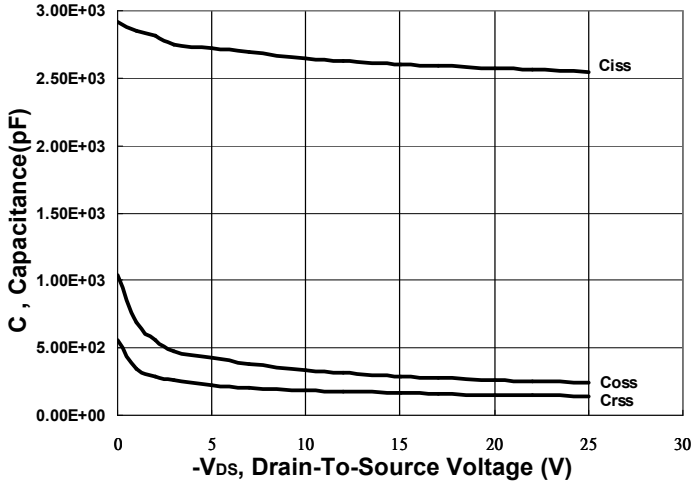
Transfer Characteristics



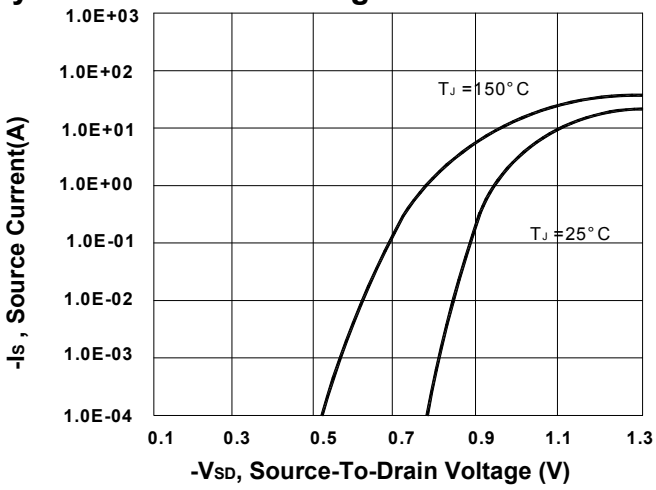
Gate charge Characteristics



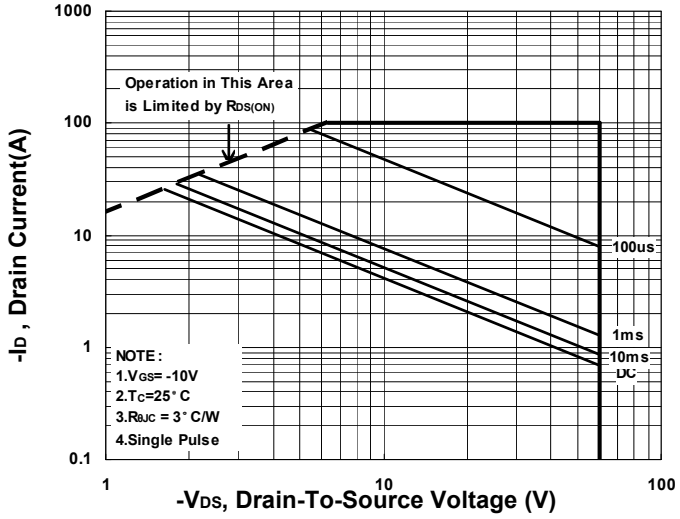
Capacitance Characteristic



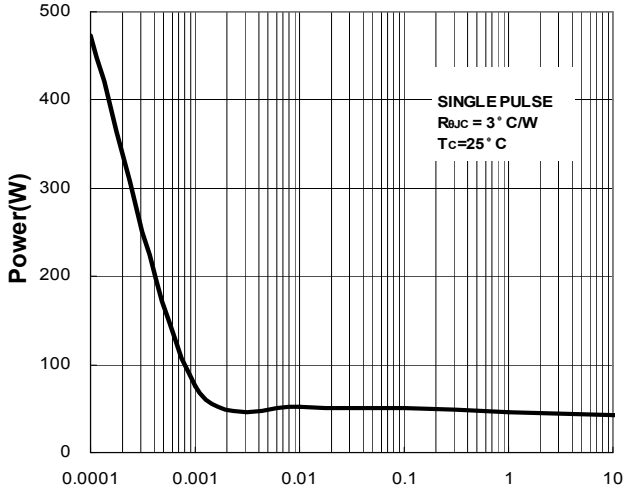
Body Diode Forward Voltage VS Source current



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve